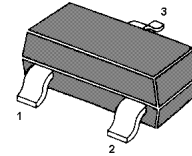


PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into five groups R, O, Y, P and L, according to its DC current gain. As complementary type the NPN transistor MMBTSC945 is recommended.



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	60	V
Collector Emitter Voltage	-V _{CEO}	50	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	150	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	-55 to +150	°C

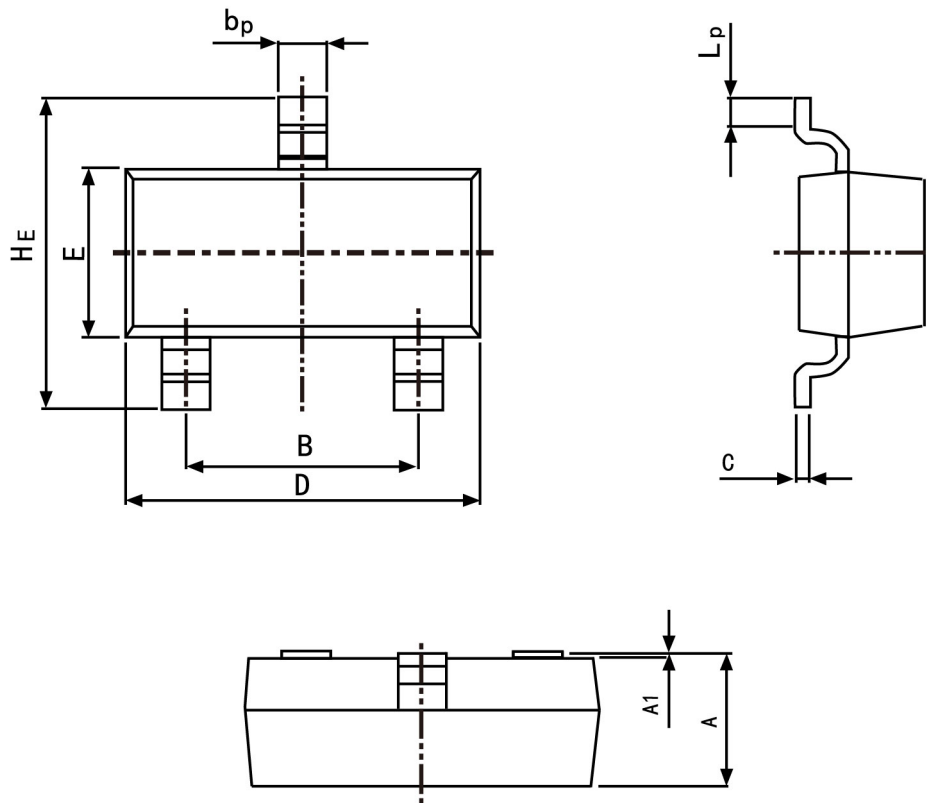
Characteristics at $T_{amb}=25\text{ °C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=6V$, $-I_C=1mA$					
Current Gain Group	R	40	-	80	-
	O	70	-	140	-
	Y	120	-	240	-
	P	200	-	400	-
	L	350	-	700	-
Collector Base Breakdown Voltage at $-I_C=100\mu A$	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C=10mA$	$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $-I_E=10\mu A$	$-V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at $-V_{CB}=60V$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}=5V$	$-I_{EBO}$	-	-	0.1	μA
Collector Saturation Voltage at $-I_C=100mA$, $-I_B=10mA$	$-V_{CE(sat)}$	-	-	0.3	V
Base Emitter Voltage at $-V_{CE}=6V$, $-I_C=1mA$	$-V_{BE(on)}$	0.5	-	0.8	V
Gain Bandwidth Product at $-V_{CE}=6V$, $-I_C=10mA$	f_T	50	180	-	MHz
Output Capacitance at $-V_{CB}=10V$, $f=1MHz$	C_{OB}	-	2.8	-	pF
Noise Figure at $-V_{CE}=6V$, $-I_C=0.3mA$, $f=100Hz$, $R_S=10K\Omega$	F	-	6	20	dB

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



SOT-2

Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.40
B	1.78	2.04
bp	0.35	0.50
C	0.08	0.19
D	2.70	3.10
E	1.20	1.65
HE	2.20	3.00
A1	0.100	0.013
Lp	0.20	0.50

ses only.